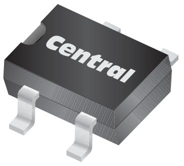
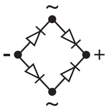
CBRSDSH1-40L

SURFACE MOUNT
HIGH DENSITY
1 AMP LOW V_F SILICON
SCHOTTKY BRIDGE RECTIFIER





SMDIP CASE

Central
Semiconductor Corp.

www.centralsemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CBRSDSH1-40L is a full wave bridge rectifier mounted in a durable epoxy surface mount molded case, utilizing glass passivated chips.

MARKING: FULL PART NUMBER

FEATURES:

- Low Leakage Current (20μA TYP @ V_{RRM})
- Low V_F Schottky Diodes (440mV MAX @ I_F=1.0A)

MAXIMUM RATINGS: (T_A=25°C unless otherwise noted)	**SYMBOL**		**UNITS**
Peak Repetitive Reverse Voltage	V_{RRM}	40	V
DC Blocking Voltage	V_R	40	V
RMS Reverse Voltage	$V_{R(RMS)}$	28	V
Average Forward Current	I_O	1.2	A
Peak Repetitive Forward Current	I_{FRM}	1.7	A
Peak Forward Surge Current	I_{FSM}	20	A
Operating Junction Temperature	T_J	-50 to +125	°C
Storage Temperature	T_{stg}	-50 to +150	°C

ELECTRICAL CHARACTERISTICS PER DIODE: (T_A=25°C unless otherwise noted)

SYMBOL	**TEST CONDITIONS**	**TYP**	**MAX**	**UNITS**
I_R	V_R=40V	20	50	μA
I_R	V_R=40V, T_A=100°C	5.0	20	mA
V_F	I_F=500mA	360	380	mV
V_F	I_F=1.0A	390	440	mV
C_J	V_R=4.0V, f=1.0MHz	150		pF

R1 (7-June 2010)

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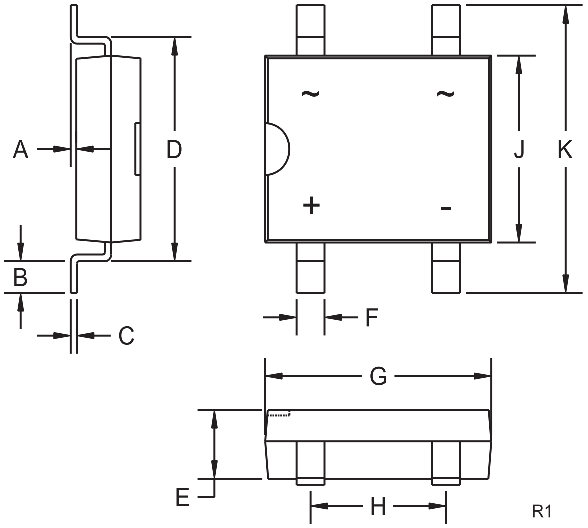
SMDIP CASE - MECHANICAL OUTLINE



DIMENSIONS				
	INCHES		MILLIMETERS	
SYMBOL	MIN	MAX	MIN	MAX
A	0.004	0.008	0.10	0.20
B	0.040	0.060	1.02	1.52
C	0.009		0.23	
D	0.290	0.310	7.37	7.87
E	0.086	0.098	2.18	2.49
F	0.038	0.042	0.97	1.07
G	0.316	0.335	8.03	8.51
H	0.195	0.205	4.95	5.21
J	0.245	0.255	6.22	6.48
K	0.360	0.410	9.14	10.41

SMDIP (REV: R1)

MARKING: FULL PART NUMBER

R1 (7-June 2010)